Sheet 2 ATTY, DOCKET NO. DIVISIONAL OF SERIAL NO. INFORMATION DISCLOSURE CITATION 10/292,583 160-386 APPLICANT NAKAMURA et al (Use several sheets if necessary) GROUP **FILING DATE** July 1, 2003 **U.S. PATENT DOCUMENTS** FILING DATE *EXAMINER SUBCLASS IF APPROPRIATE CLASS DOCUMENT NUMBER DATE NAME INITIAL 11/1994 Tamaki 5,369,289 5,247,533 9/1993 Okazaki et al 4,495,514 1/1985 Lawrence et al Kotaki et al 5,281,830 1/1994 5/1979 Charmakadze et al 4,153,905 5,285,078 2/1994 Mimura et al **FOREIGN PATENT DOCUMENTS** TRANSLATION COUNTRY SUBCLASS DOCUMENT DATE **CLASS** YES NO 03-218625 9/1991 abs Japan abs 05-013812 1/1993 Japan abs 51-85384 7/1976 Japan abs 56-81986 7/1981 Japan abs 61-144659 9/1986 Japan abs 4/1988 63-61161 Japan abs 61-87381 5/1986 Japan abs 02-229475 9/1990 Japan abs 59228776 12/1984 Japan abs 55009442 A 1/1980 Japan abs 1990-0701577 7/1990 Korea 5-211347 8/1993 Japan 3-183173 8/1991 Japan 4-68579 3/1992 Japan 5-129658 5/1993 Japan 57-111076 7/1982 Japan 1/1993 5-13816 Japan 62-2675 1/1987 Japan 62-287675 12/1987 Japan 83103775 4/1994 Taiwan 7-45867 2/1995

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